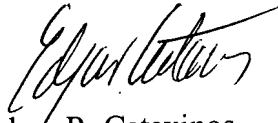


Serial No.: 10/043,468

**REMARKS**

No new matter has been added. The Applicant again requests entry of the amendments as set forth in the Appendices hereto prior to examination of the application on the merits.

Respectfully submitted,



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ERC/csw

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**VERSION OF SPECIFICATION AND ABSTRACT WITH MARKINGS  
TO SHOW CHANGES MADE**

Please replace paragraph [0001] with the following:

[0001] [Cross Reference] Cross-reference to Related [Application] Applications: This application is a continuation of application Serial No. 09/478,386, filed January 6, 2000, pending, which is a divisional of application Serial No. 09/304,368, filed May 4, 1999, now U.S. Patent 6,204,095 B1, issued March 20, 2001, which is a continuation of application Serial No. 09/056,124, filed April 6, 1998, now U.S. Patent 5,933,713, issued August 3, 1999.

Please replace the Abstract with the following:

A method for forming a semiconductor device includes forming a conductive bump on one or more of bond pads of a semiconductor substrate of a semiconductor wafer. A top or uppermost portion of each conductive bump is then planarized. The exposed portions of an active surface of the semiconductor wafer are filled with a layer of encapsulation material. The conductive bumps are reformed to their preplanarized shape and the semiconductor wafer is then diced to form singulated semiconductor dice. A preferred method of the invention also includes placing each singulated die in a mold to complete a second encapsulation step wherein a layer of encapsulation material is formed on the back surface or, alternatively, on the back and side surfaces of the semiconductor die in order to encapsulate the back, or the back and sides, of the semiconductor die. [The second encapsulation step can be accomplished either before or after the conductive bumps are reformed to their preplanarized shape, the back surface of the semiconductor wafer is layered with the encapsulating material, or the semiconductor wafer is diced.]

**VERSION OF CLAIMS WITH MARKINGS TO SHOW CHANGES MADE**

2. (Amended) The method of claim 1, wherein forming said conductive bump comprises placing a volume of solder paste on said at least one of said bond [pad]pads and reflowing said paste to form round balls.

12. (Amended) The method of claim 11, wherein said at least one singulated semiconductor die has a back and sides and further comprising forming a layer of encapsulation material on said semiconductor die to cover said back and said sides of said at least one singulated semiconductor die.

13. (Amended) The method of claim 12, wherein forming [a] said layer of encapsulation material on said back and sides of said at least one semiconductor die comprises overcoating said back and said sides of said at least one singulated semiconductor die and said conductive traces with a glass material.

14. (Amended) The method of claim 12, wherein forming [a] said layer of encapsulation material on said back and sides of said at least one semiconductor die comprises overcoating said back and said sides of said at least one singulated semiconductor die and said conductive traces with a plastic material.

15. (Amended) The method of claim 12, wherein forming [a] said layer of encapsulation material on said at least one semiconductor die comprises placing said at least one singulated semiconductor die into a second mold and injecting said encapsulation material into said second mold.

19. (Amended) The method of claim 16, wherein forming [a] said layer of encapsulation material over said back surface of said semiconductor wafer comprises overcoating said back surface of said semiconductor wafer with a glass material.

20. (Amended) The method of claim 16, wherein forming [a] said layer of encapsulation material on said back surface of said semiconductor wafer comprises overcoating said back surface of said semiconductor wafer with a plastic material.

21. (Amended) The method of claim 16, wherein forming [a] said layer of encapsulation material over said back surface of said semiconductor wafer further comprises placing said semiconductor wafer into a second mold and injecting said encapsulation material into said second mold.

24. (Amended) A method for forming an encapsulated semiconductor die having an active surface and bond pads on the active surface, the method comprising:  
forming conductive traces over an active surface of a semiconductor wafer, each of said conductive traces having a first end, a second end, a top surface, and a bottom surface, said bottom surface of said first end of each said conductive trace being in contact with at least one bond pad on said active surface of said semiconductor wafer;  
forming a conductive bump on said top surface at said second end of said conductive traces, said conductive bump having a top portion transverse to said top surface of said conductive traces;  
planarizing said top portion of said conductive bump;  
dicing said semiconductor wafer to singulate at least one semiconductor die;  
forming a layer of encapsulation material on at least a portion of [an] said active surface of said semiconductor die; and  
reforming said conductive bump to a preplanarized shape extending above said layer.

25. (Amended) The method of claim 24, wherein said at least one singulated semiconductor die has a back and sides and further comprising forming [a] said layer of encapsulation material on said semiconductor die to cover said back and said sides of said at least one semiconductor die.

26. (Amended) The method of claim 25, wherein forming [a] said layer of encapsulation material on said back and sides of said at least one semiconductor die comprises overcoating said back and said sides of said at least one semiconductor die and said conductive traces with a glass material.

27. (Amended) The method of claim 25, wherein forming [a] said layer of encapsulation material on said back and sides of said at least one semiconductor die comprises overcoating said back and said sides of said at least one semiconductor die and said conductive traces with a plastic material.

28. (Amended) The method of claim 25, wherein forming [a] said layer of encapsulation material on said at least one semiconductor die comprises placing said at least one semiconductor die into a second mold and injecting said encapsulation material into said second mold.